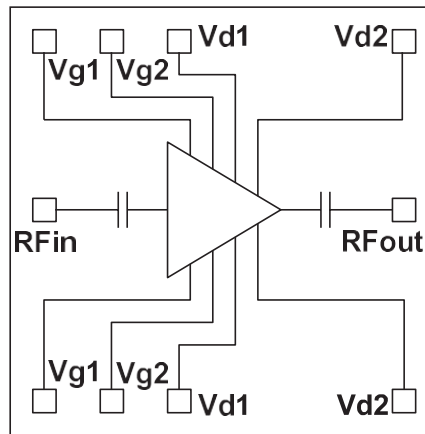


Features

- Frequency: 5-6GHz
- Gain: 26dB
- Psat: +44dBm
- Power Supply: 28V@1130mA
- Die Size : 5.1 x 4.2 mm

Typical Applications

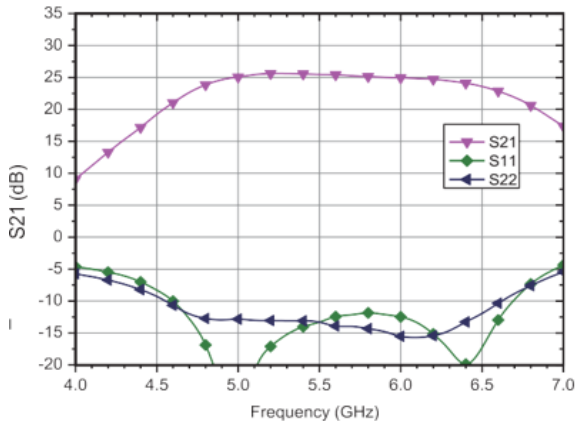
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Functional Block Diagram

Electrical Specifications

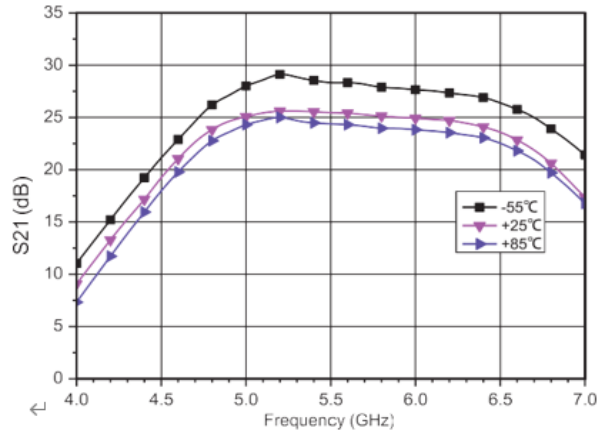
TA = +25°C, Vdd = +28V, Vgg = -2.1V (On-wafer Measurement Results)

Parameters	Min.	Typ.	Max.	Units
Frequency	5-6			GHz
Gain		26		dB
Psat		44		dBm
PAE		30		%
Input Return Loss		18		dB
Output Return Loss		14		dB
Operating Current		1130		mA

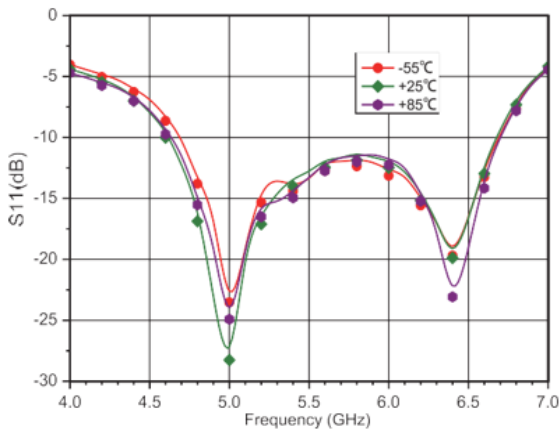
S-Parameter vs. Frequency



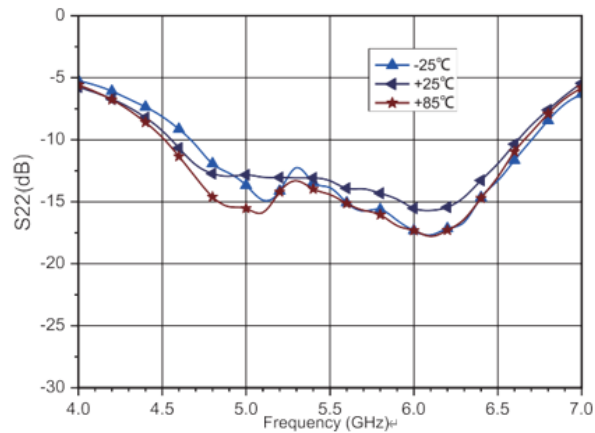
Gain vs. Frequency



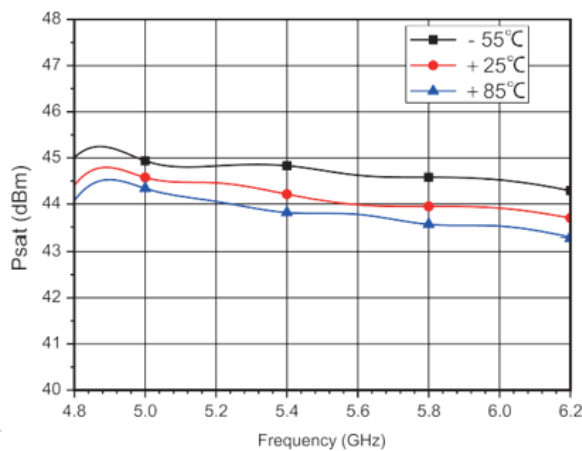
Input Return Loss vs. Frequency



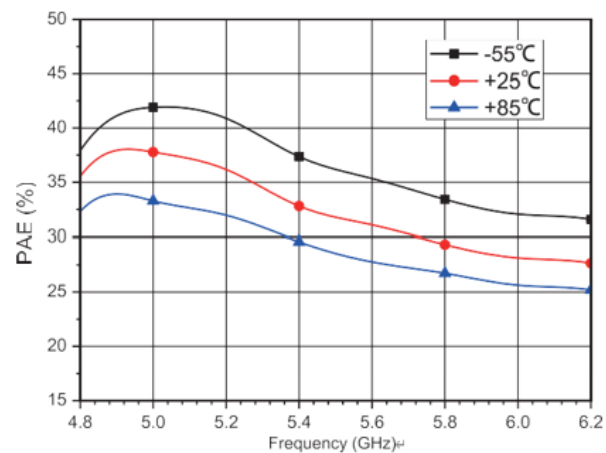
Output Return Loss vs. Frequency



Psat vs. Frequency

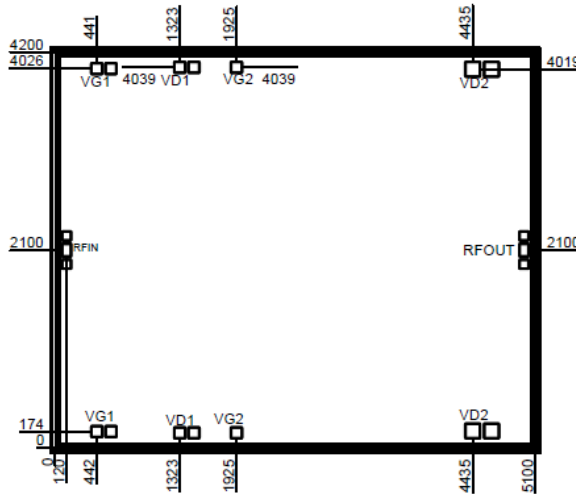


PAE vs. Frequency

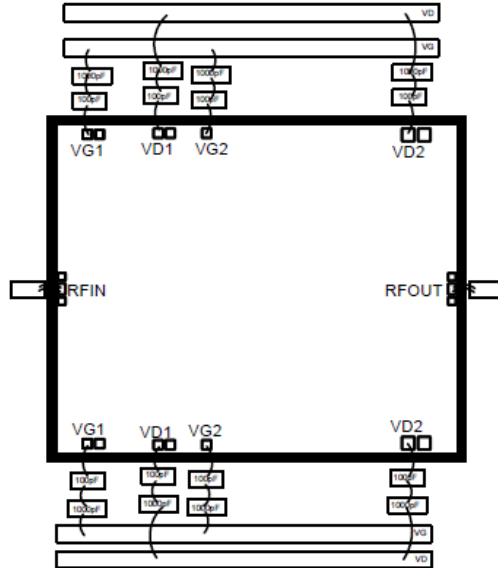




Outline Drawing: All Dimensions in μm



Assembly Drawing (Bond testing)



Notes:

1. Die thickness: 100 μm
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Supply voltage: +30V
2. RF Input power: +22dBm
3. Operating temperature: -55 $^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$
4. Storage temperature: -65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$